

Title: TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH100N6

Number: 5205/022

Issue: 4

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Paragraph: 2.5.1 Room Temperature Electrical Measurements
2.5.2 High and Low Temperatures Electrical Measurements

Original wording: See document in attachment.

Proposed wording: See document in attachment.

Justification: See document an attachment.

1) A typographical error was introduced in the DCR 794 in end of 2013 on the limits of the trr test. This error results from the characterization laboratory which inverted the test results tirm and trr. STMicroelectronics would like to return to the limits defined in the initial qualification, with some adjustment due to the increase production volume and receipt of other distribution lots. STMicroelectronics propose the new limits for the trr test on the STRH100N6 product (see proposal limits the table below).

			Room Temperature Electrical Measurements	
Product	Line	ESCC	Trr (ns) min current to New	Trr (ns) max current to New
STRH100N6	HG6K	5205022	170 to 320	260 to 480

2) STMicroelectronics would like harmonize the Vth limits for high temperature between products of the same type (N-channel). STMicroelectronics propose the new limits for the STRH100N6 product in the table below. These new limits cover the current detail specification without any impact for the customer and the products already delivered.

			High and Low Temperatures Electrical Measurements	
Product	Line	ESCC	Vth (V) min current to New	Vth (V) max current to New
STRH40N6	HG6F	5205024	1.5	3.7
STRH100N6	HG6K	5205022	1.6 to 1.5	3.5 to 3.7
STRH100N10	HG0K	5205021	1.5	3.7
STRH8N10	HG0C	5205023	1.5	3.7